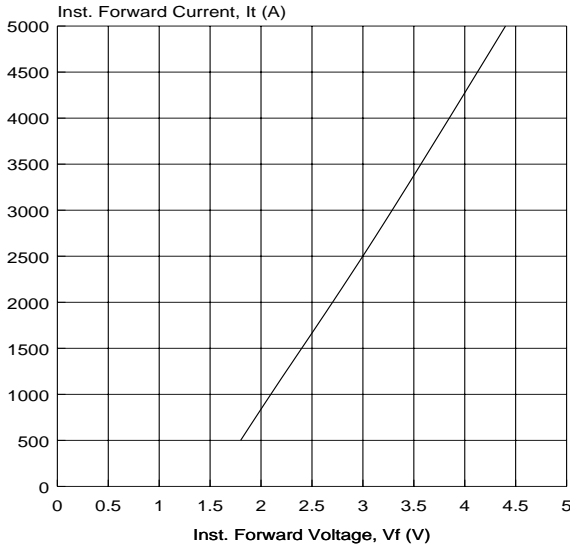


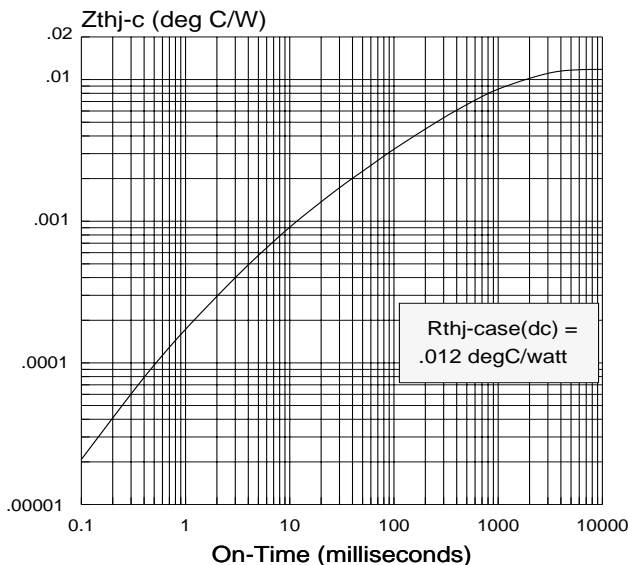
The A881B fast recovery diode is designed as parallel mate for 3000A I_{TQM} GTO's used in voltage fed inverter circuits normally requiring the bypass function. Its relatively low recovery current and charge in combination with low thermal resistance offer an advantage for optimizing other circuit components. It is manufactured by the proven multi-diffusion process with 77mm diameter silicon and is supplied in a disc-type package ready to mount using commercially available heat dissipators and clamping hardware.

FORWARD CHARACTERISTIC
Process Maximum @ T_j=125 C



11va881b

THERMAL IMPEDANCE vs. ON-TIME

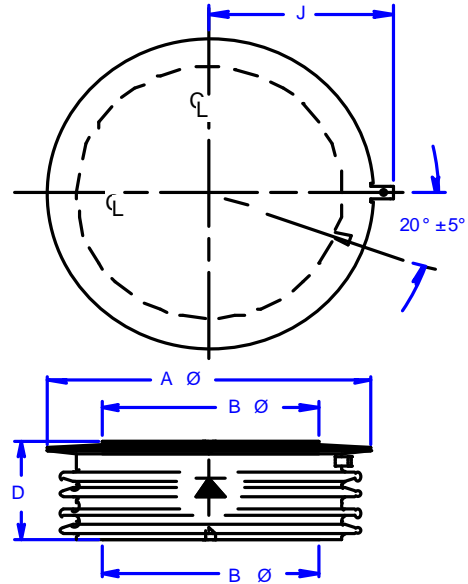


MAXIMUM RATINGS & PARAMETERS

Maximum repetitive peak reverse voltage	V _{RRM}	T _j = -40 to +125°C	4500	V
Maximum forward average & RMS current ratings	I _{F(AV)} I _{RMS}	T _{case} 70°C	1250 1950	A
Maximum reverse leakage current	I _{RRM}		200	ma
Forward voltage drop	V _{FM}	I _T = 2500A t _p = 8.3ms T _j = 125°C	3.00	V
Maximum peak recovery current*	I _{RR}	@ 100 A/us @ 400 A/us	400 1100	A
Maximum recovery charge *	Q _{RR}	@ 100 A/us @ 400A/us	1500 2725	uC

*(tested with 5UF GTO snubber)

MECHANICAL OUTLINE



A ϕ = 4.35 in (110.5 mm)
B ϕ = 2.88 in (73.2 mm)
D = 1.07 in (27.2 mm)

CLAMPING FORCE REQUIRED
7000 - 9000 lb / 31.1 - 40.0 kN